

In the Claims

Claims 1-41 (cancelled)

Claim 42 (new): A method of forming spaced conductive regions associated with a semiconductor construction, comprising:

providing a construction which includes:

a power source;

a first electrically conductive material over a semiconductor substrate, and electrically connected with the power source; and

a second electrically conductive material electrically connected with the power source only through the first electrically conductive material, the second electrically conductive material being different from the first electrically conductive material; and

utilizing the power source to remove some of the second electrically conductive material; portions of the second electrically conductive material becoming electrically isolated from the first electrically conductive material by the removal of some of the second electrically conductive material; said portions remaining as the spaced conductive regions after the power source is utilized to remove some of the second electrically conductive material.

Claim 43 (new): The method of claim 42 wherein the second electrically conductive material is oxidized during the utilizing of the power source to remove some of the second electrically conductive material; and wherein the oxidation of the second electrically conductive material is more rapid than any oxidation of the first electrically conductive material during said utilizing of the power source.

Claim 44 (new): The method of claim 42 wherein the first electrically conductive material comprises tungsten and the second electrically conductive material comprises one or more of platinum, rhodium, iridium, ruthenium.

Claim 45 (new): The method of claim 42 wherein the first electrically conductive material comprises tungsten and the second electrically conductive material comprises platinum.

Claim 46 (new): The method of claim 42 wherein the first electrically conductive material consists essentially of tungsten and the second electrically conductive material consists essentially of platinum.

Claim 47 (new): The method of claim 42 wherein the substrate comprises monocrystalline silicon.

Claim 48 (new): A method of forming capacitor constructions, comprising:

providing a substrate;

providing a first electrically conductive material over the substrate;

providing openings extending through the first electrically conductive material and into the substrate;

forming a second electrically conductive material within the openings and over the first electrically conductive material, the second electrically conductive material being different from the first electrically conductive material and being in electrical contact with the first electrically conductive material;

electrically removing some of the second electrically conductive material; the first electrically conductive material being electrically connected to a power source during the removal of some of the second electrically conductive material and the second electrically conductive material being electrically connected to the power source only through the first electrically conductive material; the second electrically conductive material within the openings becoming electrically isolated from the first electrically conductive material during the removal of some of the second electrically conductive material and remaining within the openings as spaced conductive masses after the removal of some of the second electrically conductive material;

forming dielectric material over the spaced conductive masses; and

forming capacitor electrode material over the dielectric material and capacitively separated from the conductive masses.

Claim 49 (new): The method of claim 48 wherein the first electrically conductive material comprises tungsten and the second electrically conductive material comprises one or more of platinum, rhodium, iridium, ruthenium.

Claim 50 (new): The method of claim 48 wherein at least some of the first electrically conductive material remains over the substrate after the removal of some of the second electrically conductive material; and wherein chemical-mechanical polishing is utilized to remove the remaining first electrically conductive material from over the substrate.

Claim 51 (new): A method of forming capacitor constructions, comprising:

providing a substrate comprising monocrystalline silicon and an insulative material over the monocrystalline silicon;

forming a first electrically conductive material over the substrate;

forming openings extending through the first electrically conductive material and into the insulative material;

forming a second electrically conductive material within the openings, the second electrically conductive material being different from the first electrically conductive material, the second electrically conductive material only partially filling the openings, the second electrically conductive material being in electrical contact with the first electrically conductive material;

electrically removing some of the second electrically conductive material; the first electrically conductive material being electrically connected to a power source during removal of some of the second electrically conductive material and the second electrically conductive material being electrically connected to the power source only through the first electrically conductive material; the second electrically conductive material within the openings becoming electrically isolated from the first electrically conductive material during the removal of some of the second electrically conductive material and remaining within the openings as spaced conductive masses;

removing at least some of the first conductive material from over the substrate after removing some of the second electrically conductive material;

forming dielectric material within the partially filled openings and over the spaced conductive masses; and

forming capacitor electrode material over the dielectric material and capacitively separated from the conductive masses.

Claim 52 (new): The method of claim 51 wherein the first electrically conductive material comprises tungsten and the second electrically conductive material comprises one or more of platinum, rhodium, iridium, ruthenium.

Claim 53 (new): The method of claim 51 wherein chemical-mechanical polishing is utilized to remove the first conductive material from over the substrate.

Claim 54 (new): The method of claim 51 further comprising:

forming a protective material within the partially filled openings; the protective material remaining within the openings during the removal of some of the second electrically conductive material; and

removing the protective material from within the openings prior to forming the dielectric material.

Claim 55 (new): The method of claim 54 wherein the protective material comprises photoresist.

Claim 56 (new): The method of claim 54 wherein the protective material comprises PSG.

Claim 57 (new): The method of claim 51 wherein the conductive masses have sidewall surfaces along the masses, and further comprising:

removing at least some of the substrate to expose at least portions of the sidewall surfaces of the conductive masses; and

forming the dielectric material along the exposed portions of the sidewall surfaces.

Claim 58 (new): A method of forming capacitor constructions, comprising:

providing a substrate;

forming a first electrically conductive material over the substrate;

forming a second electrically conductive material in electrical connection with the first electrically conductive material, the second electrically conductive material being different from the first electrically conductive material;

electrically connecting the second electrically conductive material to a power source through the first electrically conductive material and electrically removing some of the second electrically conductive material; portions of the second electrically conductive material becoming electrically isolated from the first electrically conductive material during the removal of some of the second electrically conductive material and remaining as spaced conductive masses associated with the substrate;

forming dielectric material over the spaced conductive masses; and

forming capacitor electrode material over the dielectric material and capacitively separated from the spaced conductive masses.

Claim 59 (new): The method of claim 58 wherein the first electrically conductive material comprises tungsten and the second electrically conductive material comprises one or more of platinum, rhodium, iridium, ruthenium.

Claim 60 (new): The method of claim 58 wherein the substrate comprises an electrically insulative material over a monocrystalline silicon base; the method further comprising forming openings extending into the electrically insulative material; and wherein the forming the second electrically conductive material comprises forming the second electrically conductive material to extend within the openings in the electrically insulative material.